NSN 5961-01-044-2669

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Inclosure Material:

Metal all transistor

Overall Length:

0.120 inches all transistor and 0.240 inches all transistor

Terminal Length:

0.500 inches all transistor

Overall Diameter:

0.192 inches all transistor and 0.222 inches all transistor

Internal Configuration:

Junction contact all transistor

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-106 all transistor

Internal Junction Configuration:

Pnp all transistor

Component Function Relationship:

Matched

Component Name And Quantity:

2 transistor

Mounting Method:

Terminal all transistor

Terminal Circle Diameter:

0.095 inches all transistor and 0.105 inches all transistor

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

-12.0 breakdown voltage, collector-to-emitter, base open all transistor

Current Rating Per Characteristic:

-80.00 milliamperes source cutoff current all transistor

Power Rating Per Characteristic:

200.0 milliwatts small-signal input power, common-collector absolute all transistor

Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius junction all transistor

Terminal Type And Quantity:

4 uninsulated wire lead all transistor

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

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